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CVD-grown graphene exfoliates relatively easily by the oxidation of the copper substrate, yet the inherent oxidation of the graphene-coated copper is conceptually fascinating and poorly understood. Here, we report the study of  $O_2$  and  $H_2O$  adsorptions at the graphene/Cu(111) interface using *ab initio* calculations. We demonstrate that intercalation can occur at the interface, via oxidation (dissociative adsorption of oxygen) near the monolayer edge sites. Graphene/Cu(111) interface has a strong oxide formation tendency; lower activation barrier for  $O_2$  and  $H_2O$  dissociation into surface oxygen and hydroxyls, respectively. Graphene adsorption energy on the oxidized surface was reduced by a factor of two (per C-atom). As rapid oxidation proceeds, molecular ( $H_2O$  or  $O_2$ ) intercalation may also occur. We propose that  $O_2$  dissociation at the graphene edges as the first step for Cu(111) oxidation, following by  $H_2O$  dissociation on the decoupling of CVD-grown graphene, other important findings can also be extracted from the interaction between graphene edges and the metal surface.